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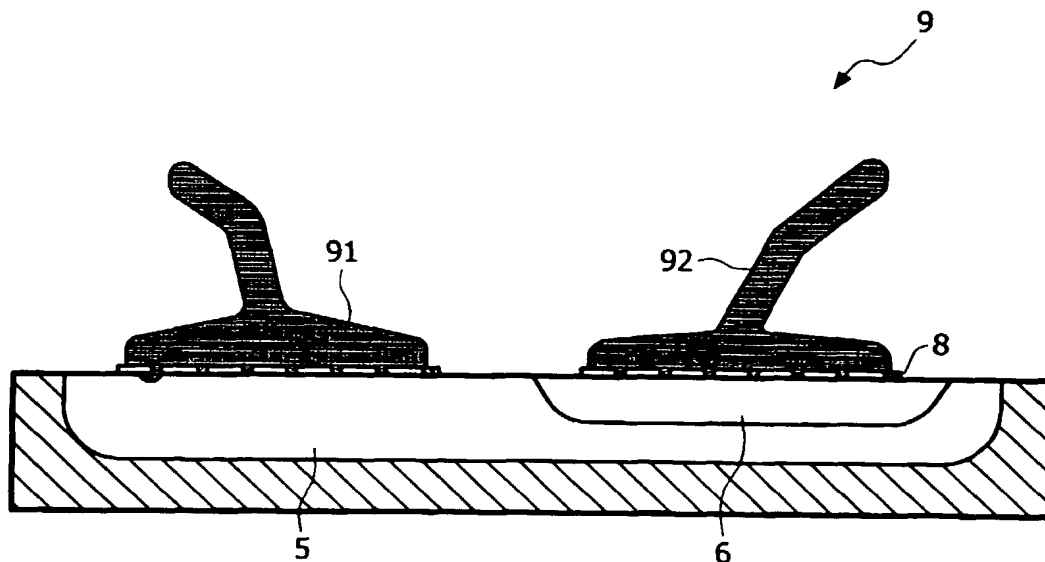
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(54) Title: WIRE-BONDED SEMICONDUCTOR COMPONENT WITH REINFORCED INNER CONNECTION METALLIZA-
TION



(57) Abstract: A semiconductor component comprising a semiconductor chip (2) made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization (7) in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection (9), characterized in that the inner connection metallization comprises a reinforcing system (8) having an open grid structure on the doped silicon substrate.



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